IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claims 1 and 5 in accordance with the following:

1. (CURRENTLY AMENDED) A semiconductor device substrate comprised of a core substrate on both main surfaces of which interconnect patterns are formed via resin layers, wherein:

the core substrate is formed by a material having a heat expansion coefficient closer to that of a semiconductor chip than ~~those~~ the respective heat expansion coefficients of the main resin layers and the interconnect patterns inside the substrate; and

a resin layer, forming an outermost layer of the substrate on each of the main surfaces thereof, of a material having at least one of a higher strength and a higher elongation than a resin material used for inner resin layers in the substrate~~, thereby~~ and preventing cracking, deformation, and other problems arising in the substrate due to ~~the~~ thermal stress occurring between the core substrate and the inner resin layers and interconnect patterns in the substrate.

2. (PREVIOUSLY PRESENTED) The semiconductor device substrate as set forth in claim 1, wherein a further resin layer, under the resin layer forming the outermost layer of the substrate, is made of a resin material having at least one of a higher strength and higher elongation than the resin material of the inner resin layers in the substrate.

3. (PREVIOUSLY PRESENTED) The semiconductor device substrate as set forth in claim 1 , wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and elongation of at least 10%.

4. (PREVIOUSLY PRESENTED) The semiconductor device substrate as set forth in claim 2, wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and elongation of at least 10%.

5. (CURRENTLY AMENDED) A semiconductor device substrate, comprising:

a core substrate on both main surfaces of which interconnect patterns are formed via resin layers;

a core substrate of a material having a heat expansion coefficient closer to that of a semiconductor chip than ~~those~~ the respective heat expansion coefficients of resin layers and interconnect patterns inside the substrate; and

a resin layer, of a material having a least one of a higher strength and a higher elongation than a resin material used for the resin layers inside the substrate, forming an outermost layer on each of the opposite main surfaces of the substrate.

6. (PREVIOUSLY PRESENTED) The semiconductor device substrate as set forth in claim 5, wherein a further resin layer, under the resin layer forming the outermost layer of the substrate, is made of a resin material having at least one of a higher strength and higher elongation than the resin material of the inner resin layers in the substrate.

7. (PREVIOUSLY PRESENTED) The semiconductor device substrate as set forth in claim 5, wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and elongation of at least 10%.

8. (PREVIOUSLY PRESENTED) The semiconductor device substrate as set forth in claim 6, wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and elongation of at least 10%.